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# ne<mark>x</mark>peria

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Low-power dual supply translating buffer

Rev. 1 — 5 June 2013

**Product data sheet** 

## 1. General description

The 74AUP1T34-Q100 provides a single buffer with two separate supply voltages. Input A is designed to track V<sub>CC(A)</sub>. Output Y is designed to track V<sub>CC(Y)</sub>. Both, V<sub>CC(A)</sub> and V<sub>CC(Y)</sub> accepts any supply voltage from 1.1 V to 3.6 V. This feature allows universal low voltage interfacing between any of the 1.2 V, 1.5 V, 1.8 V, 2.5 V, and 3.3 V voltage nodes.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V<sub>CC</sub> range from 1.1 V to 3.6 V. This device ensures a very low static and dynamic power consumption across the entire V<sub>CC</sub> range from 1.1 V to 3.6 V. This device is fully specified for partial power-down applications using I<sub>OFF</sub>. The I<sub>OFF</sub> circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

## 2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
   Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Wide supply voltage range from 1.1 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
  - JESD8-7 (1.2 V to 1.95 V)
  - JESD8-5 (1.8 V to 2.7 V)
  - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
  - MIL-STD-883, method 3015 Class 3A. Exceeds 5000 V
  - HBM JESD22-A114F Class 3A. Exceeds 5000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Wide supply voltage range:
  - ◆ V<sub>CC(A)</sub>: 1.1 V to 3.6 V
  - V<sub>CC(Y)</sub>: 1.1 V to 3.6 V
- Low static power consumption; I<sub>CC</sub> = 0.9 μA (maximum)
- Each port operates over the full 1.1 V to 3.6 V power supply range
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V<sub>CC</sub>
- I<sub>OFF</sub> circuitry provides partial Power-down mode operation



Low-power dual supply translating buffer

## 3. Ordering information

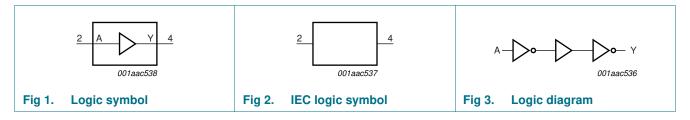
Table 1. Ordering information								
Type number	Package							
	Temperature range	Name	Description	Version				
74AUP1T34GW-Q100	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1				

## 4. Marking

Table 2. Marking	
Type number	Marking code <sup>[1]</sup>
74AUP1T34GW-Q100	pQ

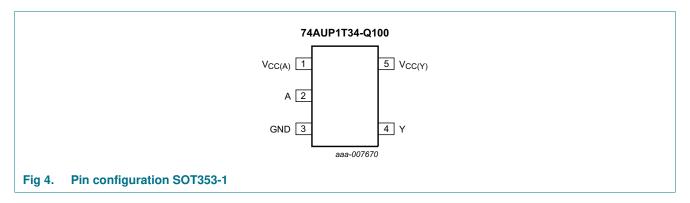
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

## 5. Functional diagram



## 6. Pinning information

### 6.1 Pinning



Low-power dual supply translating buffer

## 6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
V <sub>CC(A)</sub>	1	supply voltage port A
A	2	data input A
GND	3	ground (0 V)
Y	4	data output Y
V <sub>CC(Y)</sub>	5	supply voltage port Y

## 7. Functional description

Input	Output
Α	Y
L	L
Н	Н

[1] H = HIGH voltage level; L = LOW voltage level.

## 8. Limiting values

### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

					/
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC(A)</sub>	supply voltage A		-0.5	+4.6	V
V <sub>CC(Y)</sub>	supply voltage Y		-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>1</sub> < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	[1] -0.5	+4.6	V
lo	output current	$V_O = 0 V$ to $V_{CC(Y)}$	-	±20	mA
I <sub>CC</sub>	supply current		-	50	mA
I <sub>GND</sub>	ground current		-50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \text{ °C to } +125 \text{ °C}$	[2] _	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP5 packages: above 87.5 °C the value of  $P_{tot}$  derates linearly with 4.0 mW/K.

Low-power dual supply translating buffer

## 9. Recommended operating conditions

Table 6.	Recommended operating conditions								
Symbol	Parameter	Conditions	Min	Max	Unit				
V <sub>CC(A)</sub>	supply voltage A		1.1	3.6	V				
V <sub>CC(Y)</sub>	supply voltage Y		1.1	3.6	V				
VI	input voltage		0	3.6	V				
Vo	output voltage		0	V <sub>CC(Y)</sub>	V				
T <sub>amb</sub>	ambient temperature		-40	+125	°C				
$\Delta t/\Delta V$	input transition rise and fall rate	control and data inputs; $V_{CC(A)} = 1.1 V$ to 3.6 V	0	200	ns/V				

## **10. Static characteristics**

### Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
T <sub>amb</sub> = 2	5 °C					
V <sub>IH</sub>	HIGH-level	$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	$0.65 \times V_{CC(A)}$	-	-	V
	input voltage	$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	1.6	-	-	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
V <sub>IL</sub>	LOW-level input	$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	$0.35 \times V_{CC(A)}$	V
	voltage	$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.7	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V
V <sub>OH</sub>	HIGH-level	$V_{I} = V_{IH}$				
	output voltage	$I_{O} = -20 \ \mu\text{A}; \ V_{CC(A)} = V_{CC(Y)} = 1.1 \ V \text{ to } 3.6 \ V$	$V_{CC(Y)} - 0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	$0.75 \times V_{\text{CC}(\text{Y})}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.6	-	-	V
V <sub>OL</sub>	LOW-level	$V_{I} = V_{IL}$				
	output voltage	$I_{O}$ = 20 µA; $V_{CC(A)}$ = $V_{CC(Y)}$ = 1.1 V to 3.6 V	-	-	0.1	V
		$I_{O} = 1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	-	-	$0.3 \times V_{CC(Y)}$	V
		$I_{O} = 1.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	-	-	0.31	V
		$I_{O}$ = 1.9 mA; $V_{CC(A)} = V_{CC(Y)}$ = 1.65 V	-	-	0.31	V
		$I_{O}$ = 2.3 mA; $V_{CC(A)}$ = $V_{CC(Y)}$ = 2.3 V	-	-	0.31	V
		$I_{O} = 3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.44	V
		$I_{O} = 2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.31	V
		$I_{O} = 4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.44	V
lı	input leakage current	$V_I = 0$ V to 3.6 V; $V_{CC(A)} = V_{CC(Y)} = 1.1$ V to 3.6 V	-	-	±0.1	μA
74AUP1T34_Q1	00	All information provided in this document is subject to legal disclaimed	ers.		© NXP B.V. 2013. All rig	hts reserved.

### Low-power dual supply translating buffer

### Table 7. Static characteristics ... continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
I <sub>OFF</sub>	power-off leakage current	Input A; V <sub>I</sub> = 0 V to 3.6 V; V <sub>CC(A)</sub> = 0 V; V <sub>CC(Y)</sub> = 0 V to 3.6 V	-	-	±0.2	μA
		Output Y; $V_O = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V to 3.6 V; $V_I = 0$ V or 3.6 V; $V_{CC(Y)} = 0$ V	-	-	±0.2	μA
∆l <sub>OFF</sub>	additional power-off	Input A; $V_1 = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V to 0.2 V; $V_{CC(Y)} = 0$ V to 3.6 V	-	-	±0.2	μA
	leakage current	Output Y; $V_O = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V to 3.6 V; V <sub>I</sub> = 0 V or 3.6 V; $V_{CC(Y)} = 0$ V to 0.2 V	-	-	±0.2	μA
сс	supply current	port A; $V_I = GND$ or $V_{CC(A)}$ ; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 V \text{ to } 3.6 V$	-	-	0.5	μA
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	-	0.5	μA
		$V_{CC(A)} = 0 V; V_{CC(Y)} = 3.6 V$	-	0.0	-	μA
		port Y; $V_I = GND$ or $V_{CC(A)}$ ; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μA
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	0.0	-	μA
		$V_{CC(A)} = 0 V; V_{CC(Y)} = 3.6 V$	-	-	0.5	μA
		port A and port Y; $V_I = GND$ or $V_{CC(A)}$ ; $I_O = 0$ A; $V_{CC(A)} = V_{CC(Y)} = 1.1$ V to 3.6 V	-	-	0.5	μA
∆l <sub>CC</sub>	additional supply current	Input A; $V_{CC(A)} = 3.3$ V; $V_{CC(Y)} = 0$ V to 3.6 V; $V_I = V_{CC(A)} - 0.6$ V	-	-	40	μA
CI	input capacitance	Input A; $V_{CC(A)} = V_{CC(Y)} = 0$ V to 3.6 V; $V_I = GND$ or $V_{CC(A)}$	-	1.0	-	pF
C <sub>O</sub>	output capacitance	Output Y; $V_O = GND$ ; $V_{CC(Y)} = 0 V$ ; $V_{CC(A)} = 0 V$ to 3.6 V	-	1.8	-	pF
T <sub>amb</sub> = -	40 °C to +85 °C					
VIH	HIGH-level input voltage	$V_{CC(A)}$ = 1.1 V to 1.95 V; $V_{CC(Y)}$ = 1.1 V to 3.6 V	$0.65 \times V_{CC(A)}$	-	-	V
po lea l <sub>CC</sub> su $\Delta l_{CC}$ su $\Delta l_{CC}$ ad su $C_1$ inp Ca $C_0$ ou ca $T_{amb} = -40$ ° V <sub>IH</sub> HI inp V <sub>IL</sub> LC VOH HI		$V_{CC(A)}$ = 2.3 V to 2.7 V; $V_{CC(Y)}$ = 1.1 V to 3.6 V	1.6	-	-	V
		$V_{CC(A)}$ = 3.0 V to 3.6 V; $V_{CC(Y)}$ = 1.1 V to 3.6 V	2.0	-	-	V
VIL	LOW-level input	$V_{CC(A)}$ = 1.1 V to 1.95 V; $V_{CC(Y)}$ = 1.1 V to 3.6 V	-	-	$0.35 \times V_{CC(A)}$	V
	voltage	$V_{CC(A)} = 2.3$ V to 2.7 V; $V_{CC(Y)} = 1.1$ V to 3.6 V	-	-	0.7	V
		$V_{CC(A)}$ = 3.0 V to 3.6 V; $V_{CC(Y)}$ = 1.1 V to 3.6 V	-	-	0.9	V
V <sub>OH</sub>	HIGH-level	$V_{I} = V_{IH}$				
	output voltage	$I_{O} = -20 \ \mu\text{A}; \ V_{CC(A)} = V_{CC(Y)} = 1.1 \ V \text{ to } 3.6 \ V$	$V_{CC(Y)} - 0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	$0.7 \times V_{CC(Y)}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	1.97	-	-	V
						<b>\</b> /
		$I_{O} = -3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	1.85	-	-	V
		$\frac{I_{O} = -3.1 \text{ mA; } V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}}{I_{O} = -2.7 \text{ mA; } V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}}$	1.85 2.67	-	-	V V

Low-power dual supply translating buffer

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>OL</sub>	LOW-level	$V_I = V_{IL}$				
	output voltage	$I_O$ = 20 $\mu A;$ $V_{CC(A)}$ = $V_{CC(Y)}$ = 1.1 V to 3.6 V	-	-	0.1	V
		$I_O = 1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	-	-	$0.3\times V_{CC(Y)}$	V
		$I_O = 1.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	-	-	0.37	V
		$I_{O}$ = 1.9 mA; $V_{CC(A)} = V_{CC(Y)}$ = 1.65 V	-	-	0.35	V
		$I_{O} = 2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.33	V
		$I_{O} = 3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.45	V
		$I_{O} = 2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.33	V
		$I_{O} = 4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.45	V
1	input leakage current	$V_{I}$ = 0 V to 3.6 V; $V_{CC(A)}$ = $V_{CC(Y)}$ = 1.1 V to 3.6 V	-	-	±0.5	μA
I <sub>OFF</sub>	power-off leakage current	Input A; $V_1 = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V; $V_{CC(Y)} = 0$ V to 3.6 V	-	-	±0.5	μA
	-	Output Y; $V_O = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V to 3.6 V; V <sub>1</sub> = 0 V or 3.6 V; $V_{CC(Y)} = 0$ V	-	-	±0.5	μ <b>A</b>
ΔI <sub>OFF</sub>	additional power-off leakage current	Input A; $V_1 = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V to 0.2 V; $V_{CC(Y)} = 0$ V to 3.6 V	-	-	±0.6	μA
		Output Y; $V_O = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V to 3.6 V; V <sub>I</sub> = 0 V or 3.6 V; $V_{CC(Y)} = 0$ V to 0.2 V	-	-	±0.6	μ <b>A</b>
lcc	supply current	port A; $V_I = GND$ or $V_{CC(A)}$ ; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μA
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	-	0.9	μA
		$V_{CC(A)} = 0 V; V_{CC(Y)} = 3.6 V$	-	0.0	-	μA
		port Y; $V_I = GND$ or $V_{CC(A)}$ ; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μA
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	0.0	-	μA
		$V_{CC(A)} = 0 V; V_{CC(Y)} = 3.6 V$	-	-	0.9	μA
		port A and port Y; $V_I = GND$ or $V_{CC(A)}$ ; $I_O = 0$ A; $V_{CC(A)} = V_{CC(Y)} = 1.1$ V to 3.6 V	-	-	0.9	μ <b>A</b>
∆I <sub>CC</sub>	additional supply current	Input A; $V_{CC(A)} = 3.3$ V; $V_{CC(Y)} = 0$ V to 3.6 V; $V_I = V_{CC(A)} - 0.6$ V	-	-	50	μ <b>A</b>
T <sub>amb</sub> = –	40 °C to +125 °C					
V <sub>IH</sub>	HIGH-level	$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	$0.7\times V_{CC(A)}$	-	-	V
	input voltage	$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	1.6	-	-	V
		V <sub>CC(A)</sub> = 3.0 V to 3.6 V; V <sub>CC(Y)</sub> = 1.1 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-level input	$V_{CC(A)} = 1.1$ V to 1.95 V; $V_{CC(Y)} = 1.1$ V to 3.6 V	-	-	$0.3 \times V_{CC(A)}$	V
	voltage	$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.7	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V

### Table 7. Static characteristics ...continued

### Low-power dual supply translating buffer

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>он</sub>	HIGH-level	$V_I = V_{IH}$				
	output voltage	$I_O = -20~\mu\text{A};~V_{CC(\text{A})} = V_{CC(\text{Y})} = 1.1$ V to 3.6 V	$V_{CC(Y)}-0.11$	-	-	V
		$I_O = -1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	$0.6 \times V_{\text{CC}(\text{Y})}$	-	-	V
		$I_O = -1.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.30	-	-	V
V <sub>OL</sub>	LOW-level	$V_{I} = V_{IL}$				
	output voltage	$I_{O} = 20 \ \mu A; V_{CC(A)} = V_{CC(Y)} = 1.1 \ V \text{ to } 3.6 \ V$	-	-	0.11	V
		$I_{O} = 1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	-	-	$0.33 \times V_{CC(Y)}$	V
		$I_{O} = 1.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	-	-	0.41	V
		$I_{O} = 1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	-	-	0.39	V
		$I_{O} = 2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.36	V
		$I_{O} = 3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.50	V
		$I_{O} = 2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.36	V
		$I_{O} = 4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.50	V
I	input leakage current	$V_{I} = 0$ V to 3.6 V; $V_{CC(A)} = V_{CC(Y)} = 1.1$ V to 3.6 V	-	-	±0.75	μA
OFF	power-off leakage current	Input A; $V_I = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V; $V_{CC(Y)} = 0$ V to 3.6 V	-	-	±0.75	μA
		Output Y; $V_O = 0 V$ to 3.6 V; $V_{CC(A)} = 0 V$ to 3.6 V; $V_I = 0 V$ or 3.6 V; $V_{CC(Y)} = 0 V$	-	-	±0.75	μA
∆I <sub>OFF</sub>	additional power-off leakage current	Input A; $V_1 = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V to 0.2 V; $V_{CC(Y)} = 0$ V to 3.6 V	-	-	±0.75	μA
		Output Y; $V_O = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V to 3.6 V; V <sub>I</sub> = 0 V or 3.6 V; $V_{CC(Y)} = 0$ V to 0.2 V	-	-	±0.75	μA
CC	supply current	port A; $V_I = GND$ or $V_{CC(A)}$ ; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μA
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	-	1.4	μA
		$V_{CC(A)} = 0 V; V_{CC(Y)} = 3.6 V$	-	0.0	-	μA
		port Y; $V_I = GND$ or $V_{CC(A)}$ ; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μA
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	0.0	-	μA
		$V_{CC(A)} = 0 \text{ V}; V_{CC(Y)} = 3.6 \text{ V}$	-	-	1.4	μA
		port A and port Y; $V_I = GND$ or $V_{CC(A)}$ ; $I_O = 0$ A; $V_{CC(A)} = V_{CC(Y)} = 1.1$ V to 3.6 V	-	-	1.4	μA
∆I <sub>CC</sub>	additional supply current	Input A; $V_{CC(A)} = 3.3 \text{ V}$ ; $V_{CC(Y)} = 0 \text{ V}$ to 3.6 V; $V_I = V_{CC(A)} - 0.6 \text{ V}$	-	-	75	μA

#### Table 7. Static characteristics ... continued

Low-power dual supply translating buffer

## **11. Dynamic characteristics**

### Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 6.

Symbol	Parameter	Conditions		25 °C			-4	–40 °C to +125 °C			
				Min	Typ <mark>[1]</mark>	Max	Min	Max (85 °C)	Max (125 °C)		
C <sub>L</sub> = 5 pl	F; V <sub>CC(A)</sub> = 1.1 V to	1.3 V									
t <sub>pd</sub>	propagation delay	A to Y; see <u>Figure 5</u>	[2]								
		$V_{CC(Y)} = 1.1 V \text{ to } 1.3 V$		2.6	9.8	25.4	2.3	25.9	25.9	ns	
		$V_{CC(Y)} = 1.4 V$ to 1.6 V		2.4	7.1	15.3	2.2	16.3	16.7	ns	
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.1	6.0	12.7	1.9	13.8	14.3	ns	
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.0	5.1	9.8	2.0	10.5	10.9	ns	
		$V_{CC(Y)} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		2.1	4.7	8.8	1.9	9.1	9.3	ns	
C <sub>L</sub> = 5 pl	F; V <sub>CC(A)</sub> = 1.4 V to	1.6 V									
t <sub>pd</sub>	propagation delay	A to Y; see Figure 5	[2]								
		$V_{CC(Y)} = 1.1 V \text{ to } 1.3 V$		2.3	9.1	23.9	2.0	24.5	24.5	ns	
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.1	6.4	13.6	1.9	14.7	15.2	ns	
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		1.8	5.3	10.9	1.6	12.1	12.6	ns	
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.7	4.3	7.8	1.6	8.7	9.2	ns	
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		1.8	3.9	6.6	1.6	7.1	7.5	ns	
C <sub>L</sub> = 5 pl	F; V <sub>CC(A)</sub> = 1.65 V to	9 1.95 V									
pd	propagation delay	A to Y; see Figure 5	[2]								
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.2	8.8	23.2	1.9	23.9	24.0	ns	
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.0	6.0	13.0	1.8	14.1	14.6	ns	
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		1.8	4.9	10.3	1.5	11.4	12.0	ns	
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.6	3.9	7.2	1.5	8.0	8.5	ns	
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		1.7	3.5	5.9	1.5	6.4	6.8	ns	
C <sub>L</sub> = 5 pl	F; V <sub>CC(A)</sub> = 2.3 V to 2	2.7 V									
pd	propagation delay	A to Y; see Figure 5	[2]								
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.2	8.4	22.8	1.9	23.4	23.4	ns	
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		1.9	5.7	12.3	1.8	13.4	14.0	ns	
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		1.7	4.6	9.6	1.5	10.7	11.2	ns	
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.5	3.5	6.3	1.5	7.2	7.7	ns	
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		1.6	3.1	5.1	1.4	5.6	6.0	ns	
C <sub>L</sub> = 5 pl	F; V <sub>CC(A)</sub> = 3.0 V to 3	3.6 V									
pd	propagation delay	A to Y; see Figure 5	[2]								
		$V_{CC(Y)} = 1.1 V \text{ to } 1.3 V$		2.2	8.1	22.5	1.9	22.9	22.9	ns	
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		1.9	5.4	12.0	1.8	12.9	13.4	ns	
		V <sub>CC(Y)</sub> = 1.65 V to 1.95 V		1.7	4.3	9.2	1.5	10.2	10.7	ns	
		V <sub>CC(Y)</sub> = 2.3 V to 2.7 V		1.5	3.3	6.0	1.5	6.7	7.2	ns	
		V <sub>CC(Y)</sub> = 3.0 V to 3.6 V		1.6	2.9	4.8	1.4	5.2	5.5	ns	

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Low-power dual supply translating buffer

Symbol	Parameter	Conditions		25 °C			–40 °C to +125 °C			Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 10	$F; V_{CC(A)} = 1.1 V to$	1.3 V								
pd	propagation delay	A to Y; see Figure 5	[2]							
		$V_{CC(Y)} = 1.1 V \text{ to } 1.3 V$		2.6	10.7	27.1	2.5	27.6	27.6	ns
		$V_{CC(Y)} = 1.4 V \text{ to } 1.6 V$		2.6	7.7	16.7	2.3	17.5	17.6	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.7	6.6	13.4	2.4	14.2	14.7	ns
		$V_{CC(Y)} = 2.3 V \text{ to } 2.7 V$		2.2	5.6	10.3	2.2	11.0	11.4	ns
		$V_{CC(Y)} = 3.0 V \text{ to } 3.6 V$		2.5	5.3	9.5	2.2	9.7	10.0	ns
C <sub>L</sub> = 10 J	oF; V <sub>CC(A)</sub> = 1.4 V to	1.6 V								
propagation delay		A to Y; see Figure 5	[2]							
		V <sub>CC(Y)</sub> = 1.1 V to 1.3 V		2.4	10.0	25.6	2.2	26.1	26.1	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.4	7.0	15.0	2.0	15.8	16.4	ns
		V <sub>CC(Y)</sub> = 1.65 V to 1.95 V		2.4	5.9	11.6	2.1	12.5	13.1	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.0	4.8	8.4	1.9	9.2	9.7	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.2	4.4	7.4	1.9	7.7	8.1	ns
C <sub>L</sub> = 10	oF; V <sub>CC(A)</sub> = 1.65 V t	o 1.95 V								
pd	propagation delay	A to Y; see Figure 5								
		V <sub>CC(Y)</sub> = 1.1 V to 1.3 V		2.3	9.7	24.8	2.1	25.5	25.7	ns
		V <sub>CC(Y)</sub> = 1.4 V to 1.6 V		2.3	6.6	14.3	2.0	15.3	15.8	ns
		V <sub>CC(Y)</sub> = 1.65 V to 1.95 V		2.3	5.5	11.0	2.0	11.9	12.5	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.9	4.4	7.7	1.8	8.6	9.0	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.1	4.0	6.6	1.8	7.1	7.4	ns
C <sub>L</sub> = 10	oF; V <sub>CC(A)</sub> = 2.3 V to	2.7 V								
pd	propagation delay	A to Y; see Figure 5	[2]							
		V <sub>CC(Y)</sub> = 1.1 V to 1.3 V		2.3	9.3	24.4	2.1	25.1	25.1	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.2	6.3	13.6	1.9	14.6	15.1	ns
		V <sub>CC(Y)</sub> = 1.65 V to 1.95 V		2.2	5.1	10.3	2.0	11.2	11.7	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.8	4.1	6.9	1.8	7.7	8.2	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.0	3.6	5.8	1.7	6.3	6.6	ns
ן 10 <sub>L</sub> = 10	oF; V <sub>CC(A)</sub> = 3.0 V to	9 3.6 V								
pd	propagation delay	A to Y; see Figure 5	[2]							
		V <sub>CC(Y)</sub> = 1.1 V to 1.3 V		2.3	9.0	24.2	2.1	24.6	24.6	ns
		V <sub>CC(Y)</sub> = 1.4 V to 1.6 V		2.2	6.0	13.3	1.9	14.1	14.6	ns
		V <sub>CC(Y)</sub> = 1.65 V to 1.95 V		2.2	4.9	9.9	2.0	10.6	11.2	ns
		V <sub>CC(Y)</sub> = 2.3 V to 2.7 V		1.8	3.9	6.5	1.8	7.3	7.7	ns
		V <sub>CC(Y)</sub> = 3.0 V to 3.6 V		2.0	3.5	5.4	1.7	5.8	6.2	ns

#### Table 8. Dynamic characteristics ... continued

Low-power dual supply translating buffer

Symbol	Parameter	Conditions		25 °C			-4	0 °C to +	125 °C	Unit
				Min	Typ <mark>[1]</mark>	Max	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 15	oF; V <sub>CC(A)</sub> = 1.1 V to	1.3 V								
pd	propagation delay	A to Y; see Figure 5	[2]							
		$V_{CC(Y)} = 1.1 V \text{ to } 1.3 V$		3.0	11.5	28.6	2.8	29.2	29.2	ns
		$V_{CC(Y)} = 1.4 V \text{ to } 1.6 V$		3.1	8.3	17.3	2.7	18.6	19.1	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.8	7.1	14.1	2.7	15.2	15.8	ns
		$V_{CC(Y)} = 2.3 V \text{ to } 2.7 V$		2.6	6.1	11.1	2.7	11.6	12.1	ns
		$V_{CC(Y)} = 3.0 V \text{ to } 3.6 V$		2.9	5.7	9.9	2.6	10.3	10.6	ns
C <sub>L</sub> = 15	oF; V <sub>CC(A)</sub> = 1.4 V to	1.6 V								
t <sub>pd</sub> propagation delay		A to Y; see Figure 5	[2]							
	$V_{CC(Y)} = 1.1 V \text{ to } 1.3 V$		2.8	10.8	27.1	2.6	27.7	27.7	ns	
		$V_{CC(Y)} = 1.4 V \text{ to } 1.6 V$		2.8	7.6	15.7	2.4	17.0	17.6	ns
		V <sub>CC(Y)</sub> = 1.65 V to 1.95 V		2.5	6.3	12.3	2.4	13.5	14.1	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.3	5.3	9.2	2.4	9.9	10.3	ns
		$V_{CC(Y)} = 3.0 V \text{ to } 3.6 V$		2.6	4.9	7.8	2.3	8.3	8.7	ns
C <sub>L</sub> = 15	oF; V <sub>CC(A)</sub> = 1.65 V t	o 1.95 V								
pd	propagation delay	A to Y; see Figure 5	[2]							
		V <sub>CC(Y)</sub> = 1.1 V to 1.3 V		2.7	10.5	26.4	2.5	27.1	27.3	ns
		V <sub>CC(Y)</sub> = 1.4 V to 1.6 V		2.7	7.2	15.0	2.3	16.4	17.0	ns
		V <sub>CC(Y)</sub> = 1.65 V to 1.95 V		2.4	6.0	11.7	2.3	12.8	13.5	ns
		$V_{CC(Y)} = 2.3 V \text{ to } 2.7 V$		2.2	4.9	8.5	2.2	9.2	9.7	ns
		V <sub>CC(Y)</sub> = 3.0 V to 3.6 V		2.5	4.5	7.1	2.2	7.7	8.0	ns
C <sub>L</sub> = 15	oF; V <sub>CC(A)</sub> = 2.3 V to	2.7 V								
t <sub>pd</sub> propagation delay		A to Y; see Figure 5	[2]							
		V <sub>CC(Y)</sub> = 1.1 V to 1.3 V		2.6	10.1	26.0	2.4	26.7	26.7	ns
		V <sub>CC(Y)</sub> = 1.4 V to 1.6 V		2.7	6.9	14.3	2.3	15.7	16.3	ns
		V <sub>CC(Y)</sub> = 1.65 V to 1.95 V		2.4	5.6	10.9	2.2	12.1	12.7	ns
		$V_{CC(Y)} = 2.3 V \text{ to } 2.7 V$		2.1	4.5	7.6	2.2	8.4	8.9	ns
		V <sub>CC(Y)</sub> = 3.0 V to 3.6 V		2.4	4.1	6.2	2.1	6.8	7.2	ns
C <sub>L</sub> = 15	oF; V <sub>CC(A)</sub> = 3.0 V to	9 3.6 V								
pd	propagation delay	A to Y; see Figure 5	[2]							
		V <sub>CC(Y)</sub> = 1.1 V to 1.3 V		2.6	9.8	25.7	2.4	26.2	26.2	ns
		V <sub>CC(Y)</sub> = 1.4 V to 1.6 V		2.7	6.6	14.0	2.3	15.2	15.7	ns
		V <sub>CC(Y)</sub> = 1.65 V to 1.95 V		2.4	5.4	10.5	2.2	11.6	12.1	ns
		V <sub>CC(Y)</sub> = 2.3 V to 2.7 V		2.1	4.3	7.3	2.2	7.9	8.4	ns
		V <sub>CC(Y)</sub> = 3.0 V to 3.6 V		2.4	3.9	5.9	2.1	6.4	6.8	ns

#### Table 8. Dynamic characteristics ... continued

Low-power dual supply translating buffer

Symbol	Parameter	Conditions		25 °C		–40 °C to +125 °C			Unit	
				Min	fin Typ <sup>[1]</sup> Max		Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 30	$F; V_{CC(A)} = 1.1 V to$	1.3 V								
pd	propagation delay	A to Y; see Figure 5	[2]							
		$V_{CC(Y)} = 1.1 V \text{ to } 1.3 V$		3.7	13.7	32.9	3.5	33.5	33.5	ns
		$V_{CC(Y)} = 1.4 V \text{ to } 1.6 V$		3.6	9.8	19.5	3.6	20.9	21.4	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		3.7	8.4	15.9	3.5	17.0	17.7	ns
		$V_{CC(Y)} = 2.3 V \text{ to } 2.7 V$		3.0	7.2	12.2	3.4	12.7	13.2	ns
		$V_{CC(Y)} = 3.0 V \text{ to } 3.6 V$		3.8	6.8	10.9	3.4	12.2	12.5	ns
C <sub>L</sub> = 30	oF; V <sub>CC(A)</sub> = 1.4 V to	1.6 V								
pd	propagation delay	A to Y; see Figure 5	[2]							
		$V_{CC(Y)} = 1.1 V \text{ to } 1.3 V$		3.5	13.1	31.5	3.2	32.0	32.0	ns
		V <sub>CC(Y)</sub> = 1.4 V to 1.6 V		3.3	9.1	17.8	3.3	19.2	19.9	ns
		V <sub>CC(Y)</sub> = 1.65 V to 1.95 V		3.4	7.6	14.2	3.2	15.4	16.0	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.8	6.4	10.3	3.1	11.0	11.5	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		3.5	5.9	8.9	3.1	10.1	10.5	ns
C <sub>L</sub> = 30	oF; V <sub>CC(A)</sub> = 1.65 V t	o 1.95 V								
pd	propagation delay	A to Y; see Figure 5	[2]							
		V <sub>CC(Y)</sub> = 1.1 V to 1.3 V		3.4	12.7	30.7	3.1	31.5	31.5	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		3.2	8.8	17.2	3.2	18.7	19.3	ns
		V <sub>CC(Y)</sub> = 1.65 V to 1.95 V		3.3	7.3	13.5	3.1	14.7	15.4	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.7	6.0	9.6	3.0	10.4	10.9	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		3.4	5.6	8.2	2.9	9.4	9.8	ns
C <sub>L</sub> = 30	oF; V <sub>CC(A)</sub> = 2.3 V to	2.7 V								
pd	propagation delay	A to Y; see Figure 5	[2]							
		V <sub>CC(Y)</sub> = 1.1 V to 1.3 V		3.3	12.4	30.3	3.1	31.0	31.0	ns
		V <sub>CC(Y)</sub> = 1.4 V to 1.6 V		3.2	8.4	16.5	3.1	18.0	18.7	ns
		V <sub>CC(Y)</sub> = 1.65 V to 1.95 V		3.2	6.9	12.8	3.0	14.0	14.6	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.6	5.6	8.8	2.9	9.6	10.1	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		3.3	5.2	7.3	2.9	8.5	9.0	ns
) <sub>L</sub> = 30	oF; V <sub>CC(A)</sub> = 3.0 V to	9 3.6 V								
pd	propagation delay	A to Y; see Figure 5	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		3.3	12.0	30.0	3.1	30.5	30.5	ns
		V <sub>CC(Y)</sub> = 1.4 V to 1.6 V		3.2	8.1	16.2	3.1	17.5	18.1	ns
		V <sub>CC(Y)</sub> = 1.65 V to 1.95 V		3.2	6.7	12.4	3.0	13.4	14.1	ns
		V <sub>CC(Y)</sub> = 2.3 V to 2.7 V		2.6	5.5	8.5	2.9	9.1	9.6	ns
		V <sub>CC(Y)</sub> = 3.0 V to 3.6 V		3.2	5.0	7.0	2.9	8.1	8.5	ns

#### Table 8. Dynamic characteristics ... continued

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Symbol	Parameter	Conditions		25 °C		–40 °C to +125 °C			Unit	
			-	Min	Typ <mark>[1]</mark>	Мах	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 5 pl	F, 10 pF, 15 pF and	30 pF	'							
	power dissipation capacitance	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{\text{CC}(A)}$	[3][4]							
		$V_{CC(A)} = V_{CC(Y)} = 1.2 V$		-	3.8	-	-	-	-	pF
		$V_{CC(A)} = V_{CC(Y)} = 1.5 V$		-	3.8	-	-	-	-	pF
		$V_{CC(A)} = V_{CC(Y)} = 1.8 V$		-	4.1	-	-	-	-	pF
		$V_{CC(A)} = V_{CC(Y)} = 2.5 V$		-	4.2	-	-	-	-	pF
		$V_{CC(A)} = V_{CC(Y)} = 3.3 V$		-	4.6	-	-	-	-	pF

#### Dynamic characteristics ... continued Table 8.

[1] All typical values are measured at nominal  $V_{CC}$ .

### [2] $t_{pd}$ is the same as $t_{PLH}$ and $t_{PHL}$ .

[3] All specified values are the average typical values over all stated loads.

[4]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$ 

 $f_i$  = input frequency in MHz;

 $f_o = output frequency in MHz;$ 

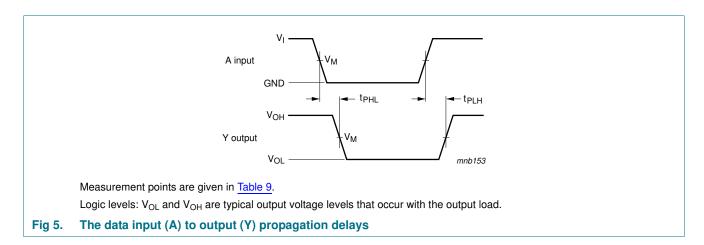
C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$  = sum of the outputs.

## 12. Waveforms

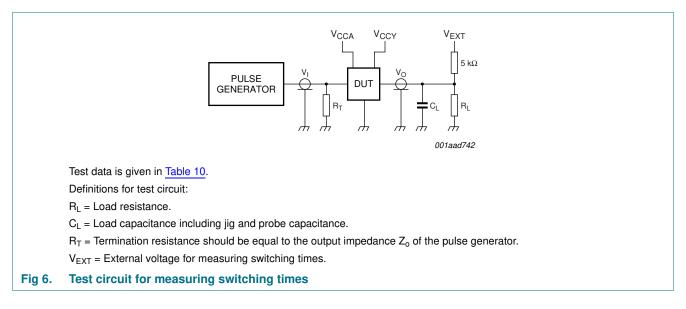


#### Table 9. **Measurement points**

Supply voltage	Output	Input		
V <sub>CC(A)</sub> /V <sub>CC(Y)</sub>	V <sub>M</sub>	V <sub>M</sub>	VI	$t_r = t_f$
1.1 V to 3.6 V	$0.5 \times V_{CC(Y)}$	$0.5\times V_{CC(A)}$	V <sub>CC(A)</sub>	$\leq$ 3.0 ns

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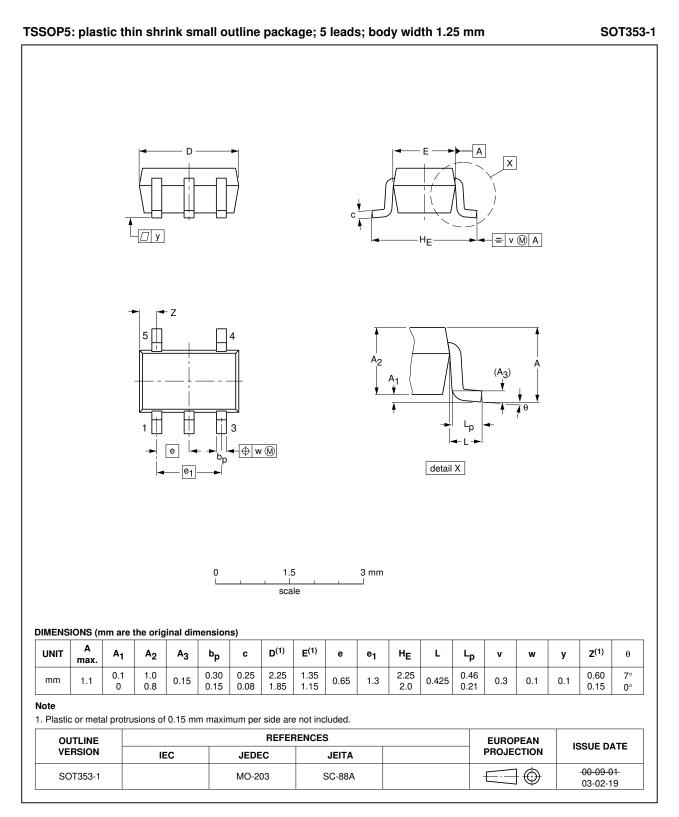
### Table 10. Test data

Supply voltage	Load		V <sub>EXT</sub>
V <sub>CC(A)</sub> /V <sub>CC(Y)</sub>	CL	R <sub>L</sub> [1]	t <sub>PLH</sub> , t <sub>PHL</sub>
1.1 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k $\Omega$ or 1 M $\Omega$	open

[1] For measuring enable and disable times,  $R_L = 5 \text{ k}\Omega$ . For measuring propagation delays, setup and hold times and pulse width,  $R_L = 1 \text{ M}\Omega$ .

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## 13. Package outline



### Fig 7. Package outline SOT353-1 (TSSOP5)

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## 14. Abbreviations

Table 11.	Abbreviations
Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MIL	Military
MM	Machine Model

## 15. Revision history

Table 12. Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes		
74AUP1T34_Q100 v.1	20130605	Product data sheet	-	-		

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## 16. Legal information

### 16.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[1] Please consult the most recently issued document before initiating or completing a design.

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